

IN THE SPECIFICATION

Please replace Table 2 on page 11 with the following amended Table 2:

Mg doped p-type GaN contact layer	0.15 μ m
Mg doped p-type Al _{0.15} Ga _{0.85} N cladding layer	0.45 μ m
Mg doped p-type GaN wave guiding layer	0.12 μ m
Mg doped p-type Al _{0.2} Ga _{0.8} N electron blocking layer	200
In _{0.03} Ga _{0.97} N/In _{0.16} Ga _{0.74} N 3-period MQWs active layer	
In _{0.10} GaN _{0.90} N well layer	35[[\square]]
In _{0.03} Ga _{0.97} N barrier layer	50[[\square]]
Si doped n-type GaN wave guiding layer	0.12 μ m
Si doped n-type Al _{0.15} Ga _{0.85} N cladding layer	0.45 μ m
Si doped n-type In _{0.1} Ga _{0.9} N	500[[\square]]
Si doped n-type GaN contact layer	3 μ m
Un-doped n-type GaN	1 μ m
Un-doped n-type ELO GaN layer	6 μ m
Un-doped GaN template layer/Si ₃ N ₄ mask	2 μ m
GaN buffer	300
Sapphire substrate	450 μ m